

Shrinking limits of silicon MOSFET's: Numerical study of 10-nm-scale devices

Y. Naveh¹ and K. K. Likharev

Department of Physics and Astronomy, State University of New York, Stony Brook, NY 11794-3800
 (February 1, 2008)

We have performed numerical modeling of dual-gate ballistic n -MOSFET's with channel length of the order of 10 nm, including the effects of quantum tunneling along the channel and through the gate oxide. Our analysis includes a self-consistent solution of the full (two-dimensional) electrostatic problem, with account of electric field penetration into the heavily-doped electrodes. The results show that transistors with channel length as small as 8 nm can exhibit either a transconductance up to 4,000 mS/mm or gate modulation of current by more than 8 orders of magnitude, depending on the gate oxide thickness. These characteristics make the devices satisfactory for logic and memory applications, respectively, though their gate threshold voltage is rather sensitive to nanometer-scale variations in the channel length.

I. INTRODUCTION

For almost half a century, the number of silicon MOSFET's on a single commercial chip has approximately doubled every eighteen months. There is little doubt that this exponential growth will continue throughout the next decade, allowing for a minimum linear scale of 50 nm at around 2010 [1]. At shorter lengths, significant technological problems arise. However, silicon MOSFET's with channel length approaching 30 nm have been studied widely in the past few years, both theoretically and experimentally (for a review see Refs. [2,3]).

A further reduction of MOSFET's linear size in bulk production will inevitably require radical advances in lithography and doping technologies, and possibly also require a change in the basic transistor geometry. However, we are not aware of any fundamental limitation on the performance of sub-30 nm scale MOSFET's. In fact, it was very recently shown [4] that a double-gate silicon-on-oxide (SOI) transistor with a gate length of 18 nm can exhibit an acceptable I_{on}/I_{off} current ratio of about eight orders of magnitude. In the present work we study theoretically transistors with even shorter gates, of length between 3 and 10 nm. We show that such devices (with channel length as short as 8 nm) can exhibit performance sufficient for both logic and memory applications.

Three fundamental differences exist between ordinary, 100-nm-scale MOSFET's, and short, 10-nm-scale devices. First, as the short channel transistors are of length comparable to or smaller than the scattering mean free path of electrons in the channel, electron transport in

them is essentially ballistic. This is in contrast to drift-diffusion transport in long transistors. Second, at 10-nm length scales, quantum mechanical tunneling can be significant, and as will be shown below, may actually dominate at some parameter range. Lastly, as the short transistors are of length comparable to the electrostatic screening length of electrons, one dimensional approximations are not sufficient to describe the electrostatic potential in the system, and a full, two-dimensional solution of the Poisson equation is required. Moreover, in contrast to long devices, we will show that finite penetration of electric field into the source, drain, and gate electrodes can crucially affect the source-drain current in the short-channel MOSFET's, and cannot be neglected.

Previous works attempting to model short-channel MOSFET's usually took into account the ballistic nature of electron transport, but relied on one-dimensional approximations, and neglected electron tunneling and finite fields in the electrodes. Natori [5] was the first to employ this approach. He calculated the I-V characteristics of both single-gate and dual-gate MOSFET's, and showed that, within this simplistic approach, the current exhibits a strong saturation due to the exhaustion of all source electrons by large source-drain voltage. Within the same approximations, Lundstrom [6] arrived at a phenomenological equation which allows for a treatment of finite backscattering of electrons. This approach was extended very recently [7], and the on-current, and in particular the effects of higher subbands on the current, were studied. However, short-channel effects such as drain-induced barrier lowering (DIBL) cannot be de-

¹e-mail: yehuda@hana.physics.sunysb.edu

scribed within this one-dimensional approximation, and therefore the authors of Ref. [7] limited themselves to devices of the order of 100 nm. A previous study by Pikus and Likharev of short-channel ballistic MOSFET's [8] also relied on a one-dimensional approximation of the electrostatics in the system, and neglected quantum tunneling and backscattering. Thus, the results of that work (mainly, that a 5-nm gate-length transistor may perform sufficiently well) could be questioned. Finally, Wong *et al.* [9] studied ballistic MOSFET's with a somewhat longer minimal channel length of around 15 nm. They concentrated on two-dimensional short channel effects, but studied only the closed state (so only the Laplace equation had to be solved). At these length scales neglect of tunneling is justified.

The aim of the present work was to model the transport in ultrashort silicon MOSFET's, with channel length of around 10 nanometers. Our modeling uses as few simplifying assumptions as possible, the main one being the neglect of backscattering, an assumption which is justified by existing mobility data, and by our choice of transistor geometry – see the next section. We take full account of the ballistic nature of transport in the transistor and of quantum mechanical tunneling. We solve the full, two-dimensional, Poisson equation not only in the channel, but also in all electrodes, thus allowing for charging effects inside the source, drain, and gates. We study both the *on* and *off* states.

II. MODEL

The geometry of the transistor under consideration in this paper is shown schematically in Fig. 1(a). As appears to be the consensus on the optimal general design for ultrasmall MOSFET's [2–4], we study here a double-gate SOI structure. A thin silicon channel of length L , width W , and thickness $t \ll W$ connects two bulk source and drain polysilicon electrodes. The electrodes are heavily doped to a donor density N_D , while the silicon layer is undoped. Both the electrodes and the channel are separated from two polysilicon gate electrodes, doped to a density N_G , by silicon oxide layers of identical thickness t_{ox} . Source-drain voltage $V = E_D - E_S$ and gate voltage $V_g = E_G - E_S$ are determined from the Fermi levels E_S , E_D , and E_G in the source, drain, and gate electrodes, respectively. A typical energy profile $\Phi(x)$ in the center of the silicon layer is shown in Fig. 1(b). Φ_0 denotes the peak of the potential energy in the channel.

Motion in the thin silicon channel is affected by lateral quantum confinement. In this work we consider only the case where the channel is so thin that E_S , E_D , and temperature T are well below the second subband energy, so only the first subband participates in transport. This assumption leads to an important aspect of our model: due to the mismatch in phase space between the strictly 2D

channel and the bulk, 3D source and drain electrodes, an electron impinging from the channel on one of the electrodes would be absorbed by that electrode, *i.e.*, would have only a negligible probability of backscattering (from source/drain impurities or phonons) into the channel [10]. If the scattering mean free path in the electrodes is larger than t then, due to the mismatch also in real space, the already negligible backscattering probability becomes even smaller.

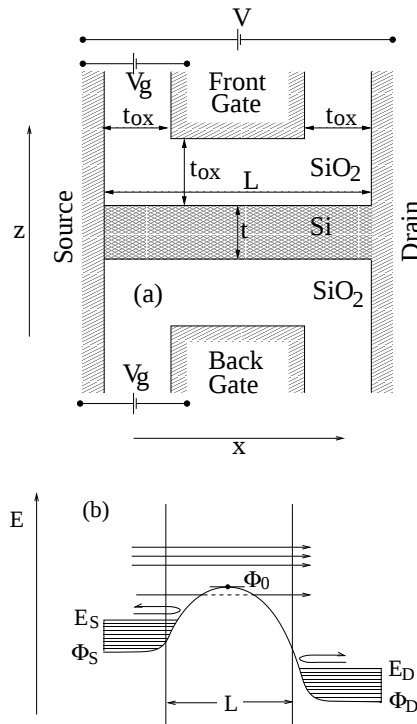


FIG. 1. (a) The model of dual-gate MOSFET used in this work. (b) General scheme of transport in ballistic transistors.

Thus, in our geometry, the usual transport model of ballistic transistors [5] holds to a very good approximation. Within this model electron distribution inside the source and drain electrodes is the equilibrium distribution at the lattice temperature T . Source electrons impinging on the channel are absorbed by it, and then travel ballistically inside the channel. However, only electrons with energy higher than Φ_0 are certain to arrive at (and be absorbed by) the drain electrode [8]. Electrons with lower energy are transmitted through the potential barrier with the quantum mechanical tunneling probability $\Theta < 1$, and reflected from it with probability $1 - \Theta$. The reflected electrons travel back ballistically towards the source electrode, where they are absorbed [see Fig. 1(b)]. A similar (but opposite) process describes the drain electrons.

All electrons in the channel and in the electrodes, as well as the ionized donors in the electrodes, contribute

to the local electrostatic potential. The self consistent solution of this Poisson-transport problem is at the heart of our calculations [11]. Once the local potential and electron density are known for any given set of V and V_g , the source-drain current I can be calculated as the difference between the source-to-drain current and the drain-to-source current [5,6,8]. The gate current due to oxide leakage can also be calculated within the regular tunneling approach.

III. THEORY

The formulation of the theory describing the above model is similar to previous works by Natori [5], Lundstrom and co-workers [6,7], and especially by Pikus and Likharev [8]. The two main differences in the theory between this and the previous works are that there is no attempt here to reduce the full Poisson equation to a one-dimensional approximation, and the source-drain tunneling current is now taken into account. Also, in the present work the quantization energy E_1 needs to be

$$\rho(x, z) = \begin{cases} -\frac{2q}{t} \cos^2\left(\frac{\pi}{t}z\right) n_2 [\Phi(x, z)] & [(x, z) \in \mathcal{C}] \\ qN_{D,G} - \frac{3(2\bar{m})^{3/2}q}{\pi^2\hbar^3} \int_{\Phi(x,z)}^{\infty} \frac{[E - \Phi(x, z)]^{1/2}}{\exp\left(\frac{E - E_F}{T}\right) + 1} dE & [(x, z) \in \mathcal{E}] \\ 0 & \text{otherwise,} \end{cases} \quad (2)$$

Where $\mathcal{C}$, $\mathcal{E}$ denote the channel and electrode (source, drain, and gate) regions, respectively, E_F is the Fermi level in the corresponding electrode, $\bar{m}$ is the three-dimensional density-of-states effective mass, and $q = |q|$ is the electron charge. The two-dimensional electron density n_2 is the sum of all partial densities of electrons at energy $E_x = \Phi(x, z) + m_1[v_x(x, z)]^2/2$, with $\mathbf{v}$ the electron velocity and m_1 the mass of the electron in the direction of the current [which, due to quantization (and assuming 100 orientation), is the light electron mass]. Counting the transmitted and reflected electrons, both from the source and the drain electrons, n_2 is given by [5,8]:

$$n_2^\pm[E_x, \Phi(x)] = -\frac{J^\pm(E_x)}{qv[E_x, \Phi(x)]}, \quad (3)$$

with $J^\pm(E_x)$ the partial current density in each direction. $J^\pm(E_x)$ is uniform throughout the length of the structure and can be calculated by using the equilibrium distribution in the source and drain electrodes. In Eq. (2) n_2 is multiplied by the cosine quantum factor in order to

taken explicitly into account because it is present only in the channel.

The basic equation to be solved in the channel, the oxide layers, and the source, drain, and gate electrodes is the Poisson equation for $\Phi(x, z)$, where x , z are the directions along and perpendicular to the channel length, respectively (see Fig. 1):

$$\nabla^2\Phi(x, z) = \frac{4\pi}{\epsilon(x, z)}\rho(x, z). \quad (1)$$

Here $\epsilon(x, z)$ is the local dielectric constant and $\rho(x, z)$ the local three dimensional charge density. The boundary conditions for Eq. (1) at $x, z \rightarrow \pm\infty$ are given in terms of the applied voltages V , V_g which determine the difference between the Fermi levels E_S , E_D , and E_G (The boundary conditions are taken at distances much larger than the screening length in the electrodes, where charge neutrality allows for a unique determination of the local potential from the known values of the local Fermi energies and donor densities).

The charge density in the structure is given by

obtain the 3D density in the channel. In the electrodes, Eq. (2) uses the equilibrium Fermi-Dirac density of electrons, while in the oxide ρ is taken to be zero.

Once equations (1) and (2) are solved simultaneously, the source-drain current can be calculated as the sum over all partial currents, each multiplied by the energy-dependent quantum transmission probability through the potential in the channel:

$$J = \frac{q}{\pi^2\hbar} \int_{-\infty}^{\infty} dk_y \int_0^{\infty} dE_x \Theta(E_x) [f_0(E) - f_0(E + V)], \quad (4)$$

where f_0 is the Fermi function,

$$E = E_1 + E_x + \frac{\hbar^2 k_y^2}{2m_1}, \quad (5)$$

and the transmission probability is given by the WKB result

$$\Theta(E_x) = \begin{cases} \exp\left\{-2 \int_{x_1}^{x_2} \frac{\sqrt{2m_1[\Phi(x) + E_1 - E_x]}}{\hbar} dx\right\} & E_x < \Phi_0 + E_1, \\ 1 & \text{otherwise,} \end{cases} \quad (6)$$

with $x_{1,2}$ the classical turning points.

We solve Eqs. (1) and (2) using a Poisson solver designed specifically for this problem. As we will see, for short devices screening in the electrodes may have a strong effect on the performance of the device. Our solver therefore treats the electrodes (source, drain, and gates) on an equal footing with the channel. This requires that we use a very small mesh size, of the order of 0.1 nm. Nonetheless, our program (which uses the conjugate gradient method [12] as its basic algorithm) works rather efficiently even with such a dense mesh. For 10-nm-scale devices, it takes a low-end workstation CPU run time of only about 3 seconds for a single iteration and less than 1 minute for the full calculation at a single parameter set.

Examples of the results of these calculations are shown in Fig. 2, where the potential energy Φ is plotted as a function of x and z for typical cases of *off* and *on* states at a finite source-drain voltage. [only $z < 0$ is shown, as $\Phi(x, z) = \Phi(x, -z)$ due to the symmetry of our geometry]. The two-dimensional short channel effects (here $L = 10$ nm) clearly manifest themselves in this figure: first, it is seen that in the *off* state [Fig. 2(a)] Φ_0 assumes a value significantly smaller than $-qV_g$. Second, in the *on* state [Fig. 2(b)] Φ_0 vanishes, and there is no longer a potential barrier in the channel. The latter effect accounts for the saturation of the current described in Refs. [5,6]. Fig. 2(c) shows the charge distribution at $z = 0$ for the same gate voltages as in panels (a,b).

IV. RESULTS

In this paper we present results for silicon *n*-MOSFET's with what we consider to be the optimal donor density and channel thickness (see the next section for a discussion) of $N_D = 3 \times 10^{20} \text{ cm}^{-3}$ and $t = 2$ nm. For these parameters, $E_1 = 96$ meV, while $E_F = 150$ meV. We study two different oxide thicknesses: the 'thin-oxide' device ($t_{ox} = 1.5$ nm) will be shown to be suitable for logic applications (for which small gate leakage is tolerable), while the 'thick-oxide' transistor ($t_{ox} = 2.5$ nm) will be suitable for memory applications, in which it is necessary to have many orders of magnitude control of the subthreshold current, while voltage gain is of minor importance. We present all results for both 'short' ($L = 8$ nm) and 'long' ($L = 12$ nm) devices.

Figure 3 shows $I - V$ characteristics of the 'thin-oxide' device for ten different values of gate voltage. The curves show a well-expressed current saturation even at $L = 8$ nm, while at $L = 12$ nm the saturation is almost flat. In these ultrasmall devices the saturation shows up only when the electron potential energy maximum in the channel is suppressed by positive gate voltage, and is due to the exhaustion of source electrons [5,6]. However, an effect which wasn't taken into account in the earlier works

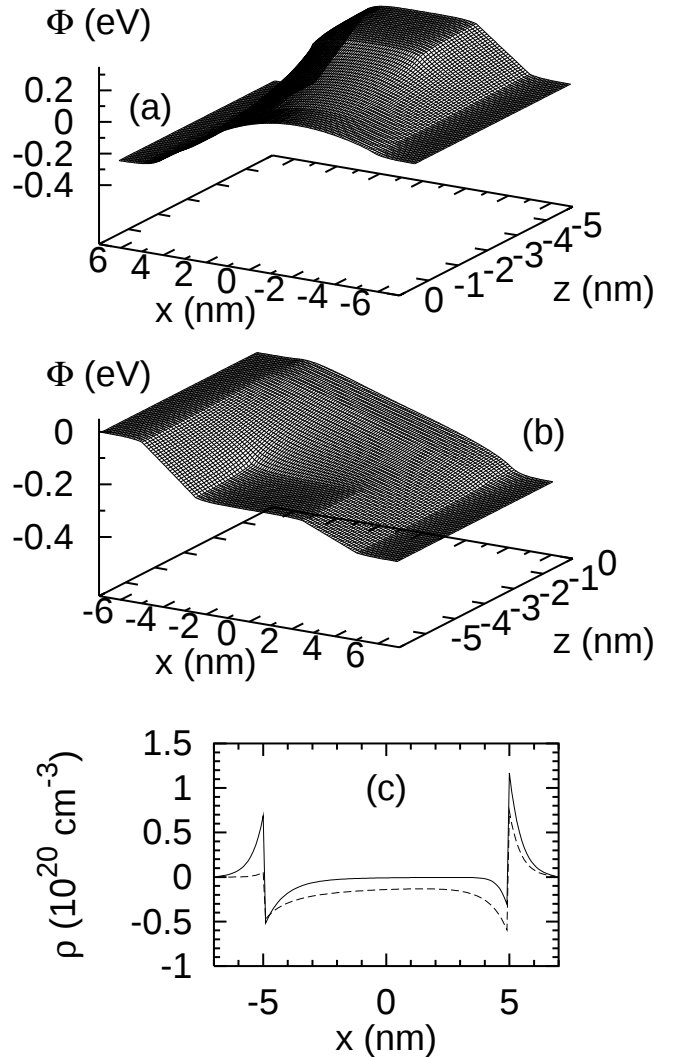


FIG. 2. Electric potential distribution in the lower half of the transistor for (a) typical negative gate voltage ($V_g = -0.3$ V) and (b) typical positive gate voltage ($V_g = 0.2$ V). (c) Charge density distributions in the center of the channel for $V_g = -0.3$ V (solid line) and $V_g = 0.2$ V (dashed line). In all three panels $L = 10$ nm, $t_{ox} = 2.5$ nm, and $V = 0.3$ V.

is the finite screening in the source and drain electrodes. As the screening length in the electrodes becomes comparable to the channel length, the voltage no longer falls only on the channel. This leads to a significant decrease of the potential energy at the source-channel interface with increasing source-drain voltage. Thus, the quantization energy E_1 (relative to the source Fermi energy E_S) is lowered with increasing V , an effect which accounts for the increase of current with V (Fig. 3) even in the 'totally saturated' regime.

Figure 4 shows the same characteristics as Fig. 3, but for the 'thick-oxide' transistor. The characteristics now

are much more linear, and saturation practically vanishes in the 8-nm length device.

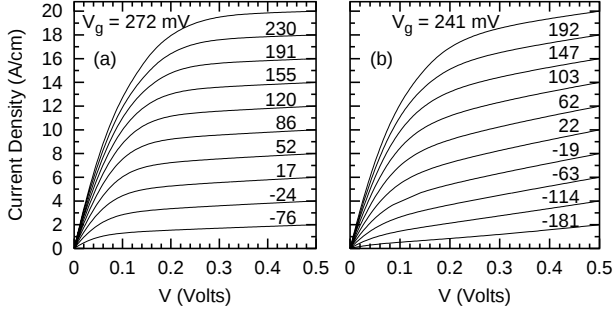


FIG. 3. Source-drain $I - V$ curves of transistors with (a) $L = 12$ nm and (b) $L = 8$ nm, for 10 values of gate voltage. Oxide thickness is $t_{ox} = 1.5$ nm.

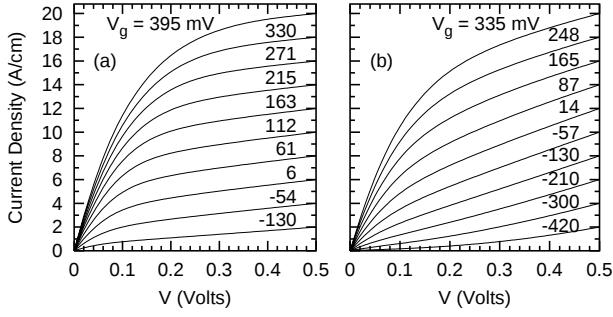


FIG. 4. Same as in Fig. 3, but for $t_{ox} = 2.5$ nm.

Sub-threshold curves of the 'thick-oxide' transistors are presented in Fig. 5 for ten different source-drain voltages. For the 12-nm device the curves have a nearly perfect log slope (indicated by the dashed line) and very small DIBL effect. However, the slope rapidly goes down and DIBL up as the length decreases below 10 nm. This loss is especially rapid at small currents (big negative gate voltages) due to electron tunneling under the narrower "bump" in the electric potential profile. Figure 6 shows the tunneling and thermal currents for the same parameters as in Fig. 5 separately (the sum of these two components gives the current presented by the upper curves of Fig. 5). It is clear from the figure that the tunneling current dominates the subthreshold current at small L (~ 8 nm) and large negative V_g . In fact, the tunneling clearly affects not only the magnitude of the current in the *off* state, but also the qualitative shape of the subthreshold curve, which is no longer exponential – see Fig. 5(b).

Also shown in Fig. 5 are the oxide-leakage current and the current due to intrinsic carriers (both are evaluated within a simple model and should be taken only as an order of magnitude estimate). Due to the large effective gap implied by the quantum confinement of electrons and holes, the latter is very small compared to the former, so

gate-oxide leakage becomes the main limiting mechanism on the subthreshold performance. Another deteriorating effect, Zener tunneling of holes from the drain electrode into the channel, appears only at negative gate voltages much larger than the ones we consider here (where the oxide leakage current is already prohibitive).

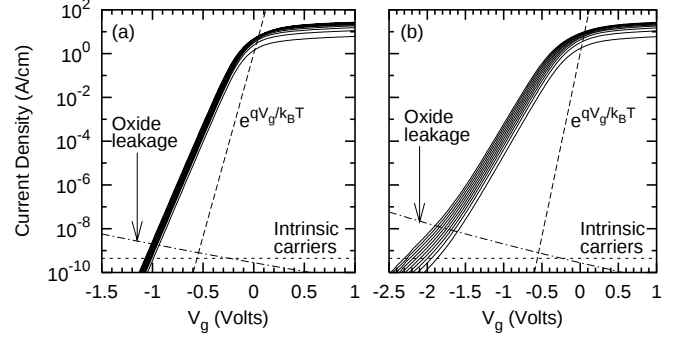


FIG. 5. Subthreshold curves for transistors with (a) $L = 12$ nm and (b) $L = 8$ nm for 10 values of source-drain voltage between $V = 0.03$ V and $V = 0.3$ V. Almost-vertical dashed lines denote the 60-mV-per-decade slope of an ideal transistor. Horizontal dashed lines represent the limit below which intrinsic carriers are not negligible. Dot-dashed lines show the current due to tunneling through the gate oxide.

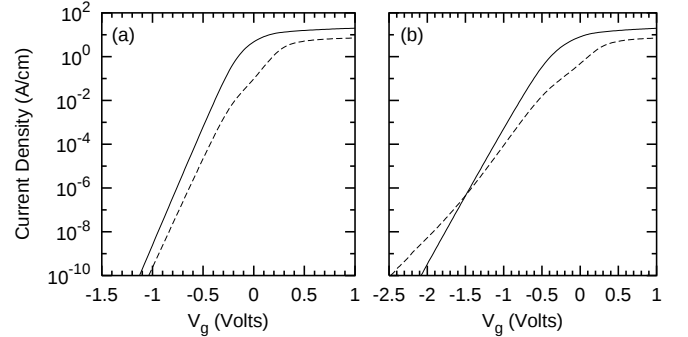


FIG. 6. Thermal (solid lines) and tunneling (dashed lines) currents as function of gate voltage at (a) $L = 12$ nm and (b) $L = 8$ nm. Here $V = 0.3$ V. All other parameters are as in Fig. 5.

Figure 7 shows subthreshold curves for the 'thin-oxide' device. The slopes of the curves in this case are almost ideal even for the short-channel device [Fig. 7(b)]. However, the large oxide leakage means that the I_{on}/I_{off} ratio is reduced to 10^{-6} .

In addition to the I_{on}/I_{off} ratio, there exist at least three other figures of merit which characterize the subthreshold curves. First is the subthreshold slope roll-off $\mathcal{S} - \mathcal{S}_{id}$, with $\mathcal{S}_{id} = 60$ mV/decade the ideal room-temperature slope. This roll-off is plotted in Fig. 8(a) as a function of L , for three values of t_{ox} .

Second is the threshold voltage roll-off $V_T - V_T^\infty$ where V_T is defined here as the gate voltage at which $J =$

2×10^{-4} A/cm and V_T^∞ is the threshold voltage at $L \rightarrow \infty$. In our geometry, $V_T^\infty = 313$ mV. The V_T roll-off is shown in Fig. 8(b) as a function of L for the same values of t_{ox} as in Fig. 8(a).

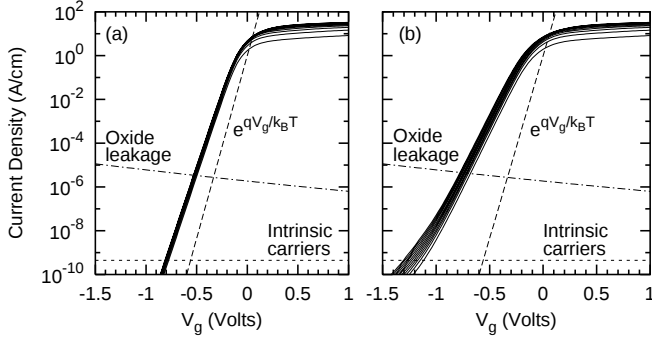


FIG. 7. Same as in Fig. 5, but for $t_{ox} = 1.5$ nm.

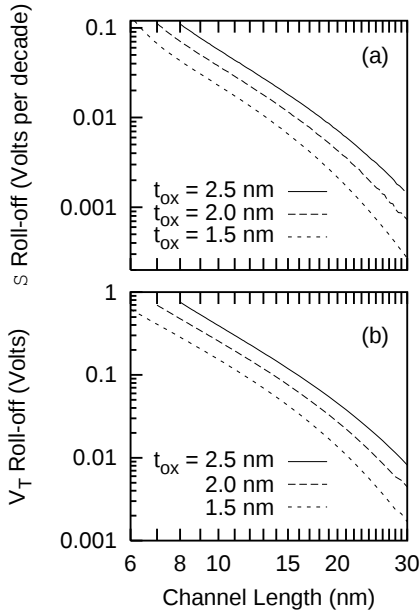


FIG. 8. (a) Subthreshold slope roll-off and (b) threshold voltage roll-off as a function of sample length for various oxide thicknesses.

Lastly, the finite value of voltage gain, defined as $G_V = (dV/dV_g)_{I=\text{const}}$, (in contrast to the “ideal” value of infinity) can be used to characterize both DIBL at the subthreshold state and imperfect saturation at the open state. Voltage gain as a function of gate voltage for both the ‘thin-oxide’ and ‘thick-oxide’ devices, and for various L ’s, is shown in Fig. 9. In order to evaluate the results here, one should remember that the usual CMOS design tools imply $G_V \gg 1$, while devices with $G_V < 1$ cannot sustain logic circuits.

In order to show the effect of channel thickness on the results, we reproduce in Fig. 10 the plots of Fig. 9 at

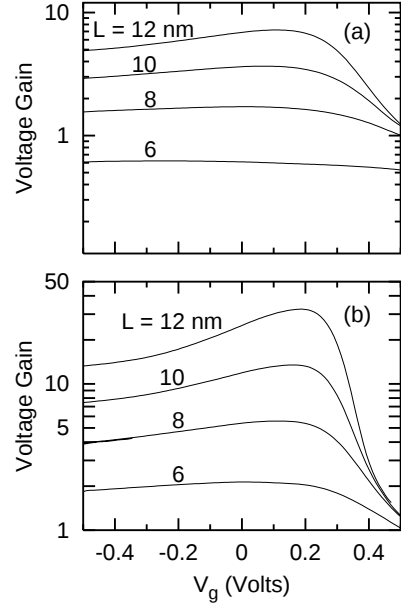


FIG. 9. Voltage gain as a function of gate voltage for various channel lengths. (a) $t_{ox} = 2.5$ nm. (b) $t_{ox} = 1.5$ nm.

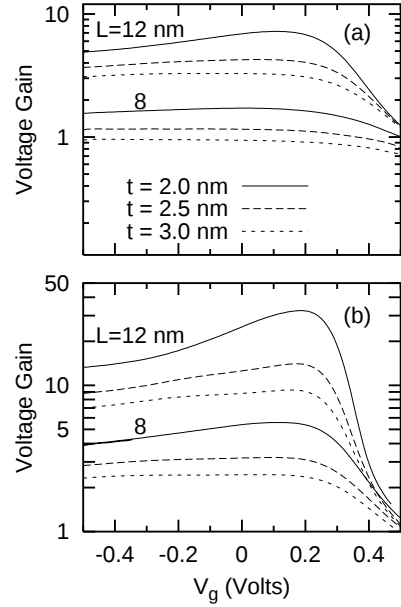


FIG. 10. Same as in Fig. 9, but for various channel thicknesses. (a) $t_{ox} = 2.5$ nm. (b) $t_{ox} = 1.5$ nm.

$L = 8$ nm and $L = 12$ nm, and include also the cases of $t = 2.5$ nm and $t = 3$ nm. At $t = 2.5$ nm our model is still strictly valid. For the sake of understanding the thickness-dependence of the performance of the device, we also present results for $t = 3$ nm, at which $E_2 = 170$ meV is higher than E_S by only 20 meV. At this and larger values of t , the second quantized level becomes too close to the source Fermi energy, so transport through the second subband (possible at finite bias via tunneling of source electrons into the second subband inside the

channel) may not be negligible.

V. DISCUSSION AND CONCLUSIONS

The main conclusion which can be drawn from our results is that ballistic, dual-gate transistors with channels as short as 8 nm still seem suitable for digital applications, with proper choice of the gate oxide thickness. In fact, devices with a relatively thick oxide allow a very high I_{on}/I_{off} ratio, above 8 orders of magnitude [Fig. 5(b)], making them suitable for memory applications including both DRAM and NOVORAM [13]. In contrast, transistors with thinner gate oxides (say, 1.5 nm) have a gate oxide leakage too high for memory applications [Fig. 7(b)], but their transconductance of about 4000 mS/mm [Fig. 3(b)] and voltage gain of around 5 over a wide range of gate voltages [Fig. 9(b)] are sufficient for logic circuits. The performance of the devices, both for logic and memory applications, improves dramatically when going from $L = 8$ nm to $L = 12$ nm [Figs. 3(a), 5(a), 9(b)]. The results presented here are compatible with the results of Ref. [8] (when comparing gate lengths), Ref. [9] (in which MOSFET's with larger t have been studied), and Ref. [7] (in which the open-state current in longer devices has been calculated within a simplified 1D model.)

At least in the geometry which we study here, a channel length of 8 nm seems to be very close to the lower limit of still-feasible MOSFET's. Most importantly, the maximal voltage gain drops to 2 already at 6 nm even for the 'thin-oxide' device [Fig. 9(b)], a fact which renders it useless for logic applications. As for memory applications, they are basically limited by the minimal thickness of the gate insulator. As long as the insulator used is SiO_2 , t_{ox} cannot be significantly thinner than 2.5 nm, which is the thinnest layer which still gives an eight-orders-of-magnitude control over the current [Fig. 5(b)]. This implies a strict limit of 5 nm on the channel length. However, a working device of $L = 6$ nm is hard to imagine, because even if a gate length of 1 nm becomes plausible, the extrapolation of the upper curve of Fig. 8(a) implies an extremely large gate voltage swing of around 5 V.

Decreasing the channel thickness t would have a desirable effect on the electrostatics of both thick- and thin-oxide devices. However, it seems that the overall effect of reducing t below 2 nm would be deteriorating. First, in layers of such small thickness, the mobility of electrons is expected to decrease sharply with decreasing t [2,14,15]. In fact, recent simulations [15] predicted the electron mobility μ in SOI MOSFET's to be around 350 cm^2/Vs at an effective electric field of 6×10^5 V/cm. This electric field corresponds to a confinement potential with a first quantized level of width $t' = 2$ nm. $\mu = 350$ cm^2/Vs implies a scattering length $l \approx 20$ nm, which is consistent with our ballistic model at $L < 15$ nm (it is

also consistent with the measurements of Ref. [4] which find mobilities of the order of 200 cm^2/Vs in MOSFET's with $t' \approx 1.5$ nm). However, at $t \approx t' \ll 2$ nm, mobility is expected to become much smaller than these values, implying a scattering length smaller than L , which is inconsistent with our model, and which would deteriorate the device due to strong backscattering.

It is worth emphasizing that for short devices ($L \approx 8$ nm), tunneling current is large, and in fact may dominate over the thermal current [Fig. 6(b)]. In this sense, one can classify the short-channel devices studied here as "tunneling transistors". The tunneling effect indeed changes the overall shape of the current characteristics [*e.g.*, the subthreshold curve is no longer exponential, see Fig. 5(b)], but even in the strong-tunneling regime the transistor is still responsive to gate voltage, enough to allow practical current-control.

One important drawback of the devices studied here is the small (or even negative) threshold voltage V_T (see Figs. 5,7). The main cause of this effect (in addition to the regular short-channel effects [2,16] which reduce V_T due to two-dimensional charge redistribution in the gate) is the undoped channel. This leads to an accumulation of electrons in the channel starting at small negative gate voltage (in contrast to regular n-channel MOSFET's with p-type substrate in which electron accumulation in the channel is possible only after the substantial depletion of holes by positive gate voltage.)

Two different approaches may be utilized to solve this problem (which is of importance mainly to logic applications). One approach is to allow a finite number of acceptor dopants in the channel. This would have an effect similar to the p-substrate in regular MOSFET's, since the gate voltage would first have to deplete the access holes before allowing for accumulation of electrons. A crude estimate of this effect can be obtained by using the planar capacitance model by which the change in V_T is given by

$$\Delta V_T = \frac{4\pi q N_a t_{ox}}{\epsilon_{ox}}, \quad (7)$$

with N_a the sheet density of acceptors, ϵ_{ox} the dielectric constant of SiO_2 , and $4\pi t_{ox}/\epsilon_{ox}$ the gate capacitance (this approximation neglects any short-channel effects). In order to achieve $\Delta V_T = 0.4V$ (which would give according to Fig. 7 $V_T \approx 0.1V$, which is sufficiently large because of the small source-drain voltages in use), N_a should be approximately $6 \times 10^{12} \text{ cm}^{-2}$, which implies $l \approx 4$ nm. Such channel doping is unacceptable since the relation $l \sim L$ implies strong fluctuations in device performance due to dopant fluctuations [17]. Thus, it seems that a more realistic approach to manipulating V_T would be to use a specific metal with necessary workfunction as a gate material.

The practical implementation of the remarkable MOSFET scaling opportunities presented here requires several

technological problems to be solved. First of all, the fabrication of dual-gate transistors requires rather advanced techniques - see, *e.g.* Ref. [18]. Second, the gate voltage threshold V_T of nanoscale transistors is rather sensitive to nanometer fluctuations of the channel length - see Fig. 8(b). Notice, however, that the *relative* sensitivity of V_T [which may be adequately characterized by the log-log plot slope $(L/V_T) \times dV_T/dL$] *decreases* at small L . This fact gives hope that with appropriate transistor geometry (for example, vertical structures where L is defined by layer thickness rather than by patterning - see, *e.g.*, Ref. [19]) the channel length fluctuations will eventually be made small enough for appreciable VLSI circuit yields.

VI. ACKNOWLEDGMENTS

Helpful discussions with D.J. Frank, C. Hu, S. Laux, M. Fischetti, J. Palmer, Y. Taur, S. Tiwari, H.-S.P. Wong, R. Zhibin, and especially M. Lundstrom and P. M. Solomon are gratefully acknowledged. This work was supported in part by the AME program of DARPA via ONR.

-
- [1] Semiconductor Industry Association, "International Technology Roadmap for Semiconductors", <http://www.semichips.org>.
 - [2] Y. Taur, D. A. Buchanan, W. Chen, D. J. Frank, K. E. Ismail, S.-H. Lo, G. A. Sai-Halasz, R. G. Viswanathan, H.-J. C. Wann, S. J. Wind, and H.-S. Wong, *Proc. IEEE* **85**, 486 (1997).
 - [3] H.-S. P. Wong, D. J. Frank, P. M. Solomon, C. H. J. Wann, and J. J. Welser, *Proc. IEEE* **87**, 537 (1999).
 - [4] X. Huang, W.-C. Lee, C. Kuo, D. Hisamoto, L. Chang, J. Kedzierski, E. Anderson, H. Takeuchi, Y.-K. Choi, K. Asano, V. Subramanian, T.-J. King, J. Bokor, and C. Hu, "Sub 50-nm FinFET: PMOS," 1999 IEDM Techn. Dig., to be published.
 - [5] K. Natori, *J. Appl. Phys.*, **76**, 4879 (1994).
 - [6] M. Lundstrom, *IEEE Electron. Device Lett.*, **18**, 361 (1997).
 - [7] F. Assad, Z. Ren, D. Vasileska, S. Datta, and M. Lundstrom, "On the performance limits for Si MOSFET's: A theoretical study", *IEEE Trans. Electron Devices*, to be published.
 - [8] F. G. Pikus and K. K. Likharev, *Appl. Phys. Lett.*, **71**, 3661 (1997).
 - [9] H.-S. P. Wong, D. J. Frank, and P. M. Solomon, 1998 IEDM Techn. Dig., 407 (1998).
 - [10] See, *e.g.*, P. M. Solomon, "On Contacts to Small Semiconductor Devices," unpublished.
 - [11] The exponentially small density of tunneling electrons below the potential barrier is neglected in our actual solution of the Poisson equation.
 - [12] W. H. Press, S. A. Teukolsky, W. T. Vetterling, and B. P. Flannery, "*Numerical Recipes in C*" (Cambridge University Press, Cambridge, 1992).
 - [13] K. K. Likharev, *Proc. IEEE*, **87**, 606 (1999).
 - [14] D. Vasileska and D. K. Ferry, *IEEE Trans. Electron Devices*, **44**, 577 (1997).
 - [15] F. Gámiz, J. A. López-Villanueva, J. B. Roldán, J. E. Carceller, and P. Cartujo, *IEEE Trans. Electron. Devices*, **45**, 1122 (1998).
 - [16] T. A. Fjeldly and M. Shur, *IEEE Trans. Electron. Devices*, **40**, 137 (1993).
 - [17] See, *e.g.*, C. Bowen, C. L. Fernando, G. Klimeck, A. Chatterjee, D. Blanks, R. Lake, J. Hu, J. Davis, M. Kulkarni, S. Hattangady, and I.-C. Chen, "Dopant Fluctuations and Quantum Effects in Sub-0.1 μ m CMOS", in *Proceedings of the 1997 International Semiconductor Device Research Symposium*, p. 1, December, 1997.
 - [18] S. Tiwari, J. J. Wesler, A. Kumar, and S. Cohen, *DRC'99 Dig.*, 26 (1999).
 - [19] K. Nakazato, K. Itoh, H. Mizuta, and H. Ahmed, *DRC'99 Dig.*, 132 (1999).